

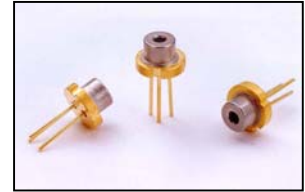
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RLT7805MG TECHNICAL DATA



Infrared Laserdiode

Structure: **AlGaAs**, index guided, quantum well

Lasing wavelength: **785 nm typ.**

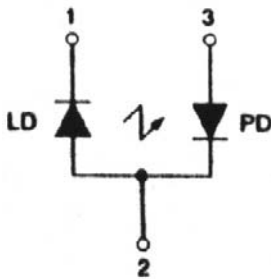
Max. optical power: **6 mW cw**

Package: **5.6 mm**

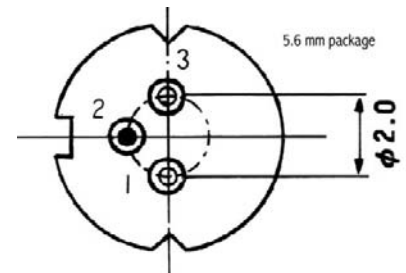


NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power cw	P _o	6	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-40 .. +60	°C
Storage Temperature	T _{STG}	-40 .. +80	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	kink free		5		mW
Threshold Current	I _{th}	cw		20	30	mA
Operation Current	I _{op}	P _o = 5 mW		30	40	mA
Operating Voltage	V _{op}	P _o = 5 mW		1.9	2.3	V
Lasing Wavelength	λ _p	P _o = 5 mW	770	785	800	nm
Beam Divergence	θ _{//}	P _o = 5 mW	8	11	15	°
Beam Divergence	θ _⊥	P _o = 5 mW	25	34	40	°
Slope Efficiency	η	P _o = 5 mW	0.3	0.5	0.7	mW/mA
Monitor Current	I _m	P _o = 5 mW, V _r =5V	0.1	0.3	0.6	mA